

isc N-Channel MOSFET Transistor

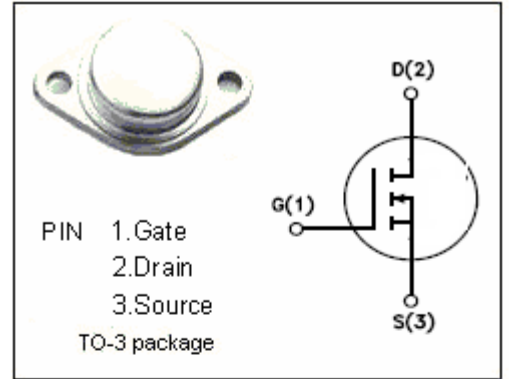
2N6764

DESCRIPTION

- VGS Rated at ±20V
- Silicon Gate for fast switching speeds
- IDSS、RDS(ON) . specified at elevated temperature
- Low drive requirements

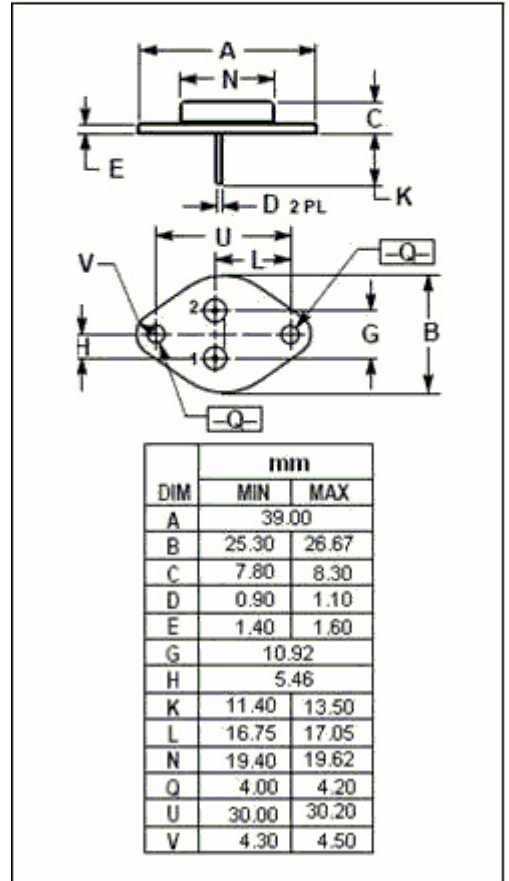
APPLICATIONS

designed for high power ,high speed application ,such as switching applies,UPS,AC and DC motor controls , relay and high energy pulse circuits.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37°C	38	A
P _{tot}	Total Dissipation@TC=25°C	150	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	0.83	°C/W

isc N-Channel Mosfet Transistor**2N6764****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	100		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 24A		0.055	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = 20V; V _{DS} = 0		100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V; V _{GS} = 0		1	mA
V _{SD}	Diode Forward Voltage	I _F = 38A; V _{GS} = 0		1.9	V